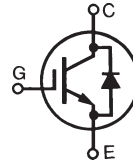


BiMOSFET™ Monolithic Bipolar MOS Transistor

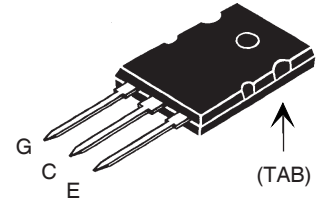
IXBK75N170A IXBX75N170A

$V_{CES} = 1700V$
 $I_{C90} = 65A$
 $V_{CE(sat)} \leq 6.00V$
 $t_{fi(typ)} = 60ns$

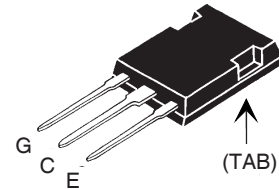


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	110	A
I_{C90}	$T_C = 90^\circ C$	65	A
I_{CM}	$T_C = 25^\circ C$, 1ms	300	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$	$I_{CM} = 100$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \cdot V_{CES}$	
P_C	$T_C = 25^\circ C$	1040	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_c	Mounting Force (PLUS247)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXBK)



PLUS247™ (IXBX)



G = Gate C = Collector
 E = Emitter TAB = Collector

Features

- International Standard Packages
- High Blocking Voltage
- Fast Switching
- High Current Handling Capability
- Anti-Parallel Diode

Advantages

- High Power Density
- Low Gate Drive Requirement
- Intergrated Diode Can Be Used for Protection

Applications

- Switched-Mode and Resonant-Mode Power Supplies
- UPS
- AC Motor Drives
- Substitutes for High Voltage MOSFETs

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 1.5mA$, $V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 42A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	4.95	5.15	6.00 V V

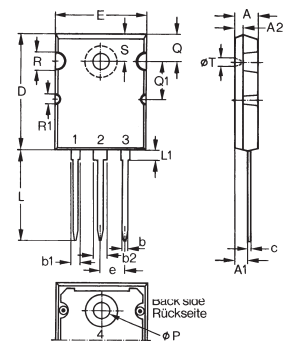
Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
g_{fs}	$I_C = 42\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	28	48		S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		7200		pF
C_{oes}			450		pF
C_{res}			150		pF
Q_g	$I_C = 42\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		358		nC
Q_{ge}			46		nC
Q_{gc}			148		nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 42\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 1\Omega$ Note 2		26		ns
t_{ri}			40		ns
$t_{d(off)}$			418		ns
t_{fi}			60	110	ns
E_{off}			3.80	7.00	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 42\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 1\Omega$ Note 2		27		ns
t_{ri}			38		ns
$t_{d(off)}$			420		ns
t_{fi}			175		ns
E_{off}			6.35		mJ
R_{thJC}				0.12	$^\circ\text{C/W}$
R_{thCS}			0.15		$^\circ\text{C/W}$

TO-264 AA (IXBK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.	
V_F	$I_F = 42\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$			4.2	V
t_{rr}	$I_F = 42\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		360		ns
I_{RM}			19		A
Q_{RM}	$V_R = 100\text{V}, V_{GE} = 0\text{V}$		3.5		μC

Notes:

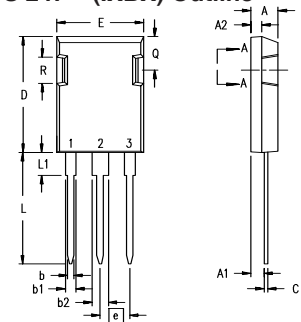
1. Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G .

Additional provisions for lead-to-lead isolation are required at $V_{CE} > 1200\text{V}$.

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

PLUS 247™ (IXBX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ 25°C

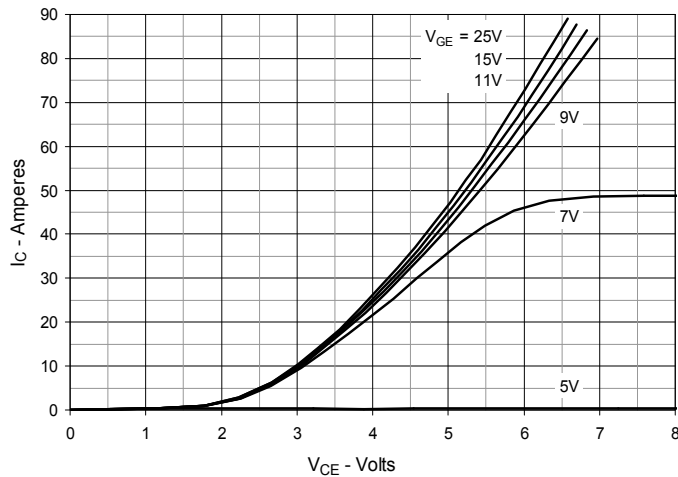


Fig. 2. Extended Output Characteristics @ 25°C

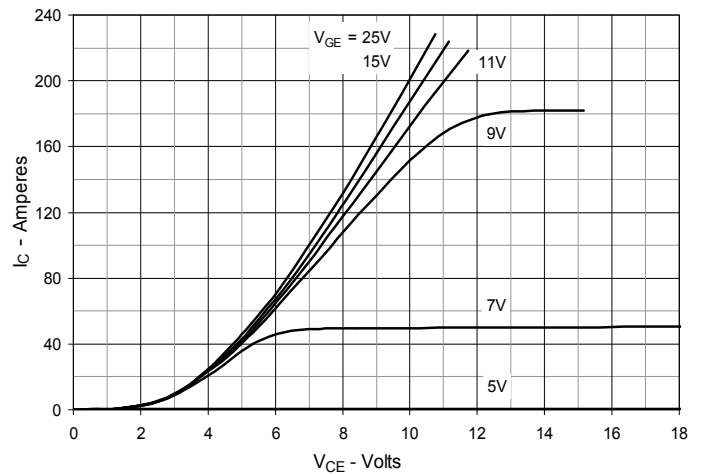


Fig. 3. Output Characteristics @ 125°C

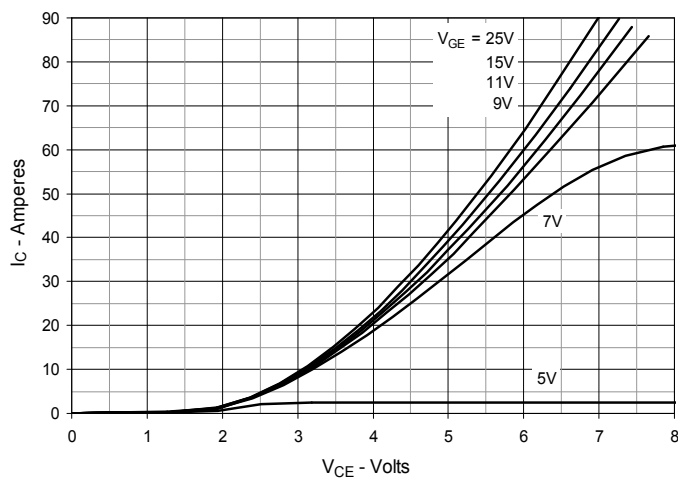


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

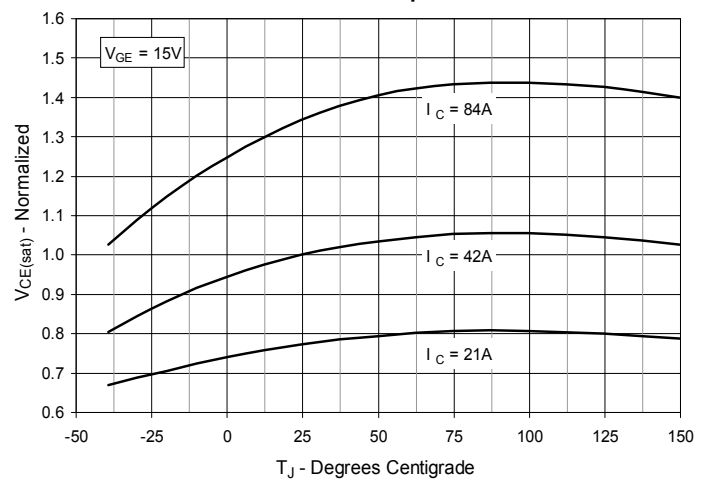


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

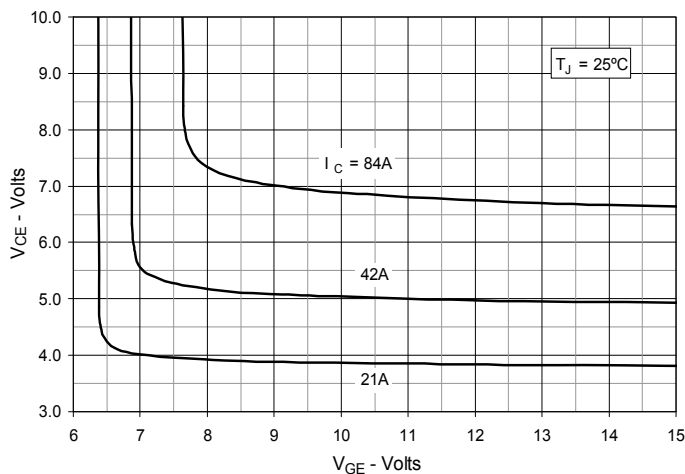


Fig. 6. Input Admittance

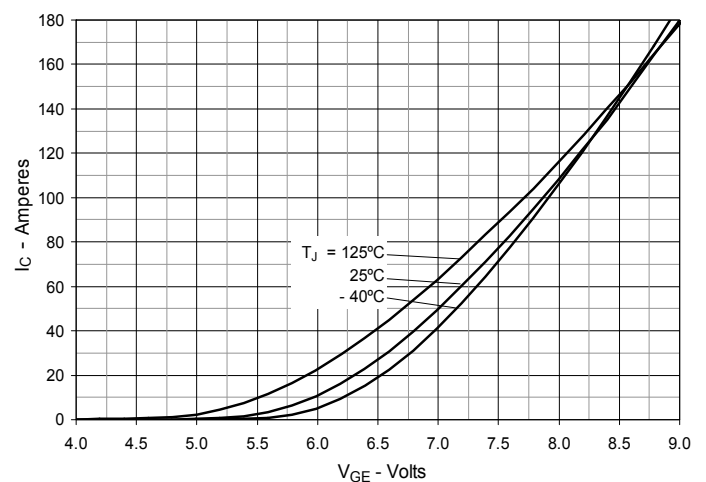


Fig. 7. Transconductance

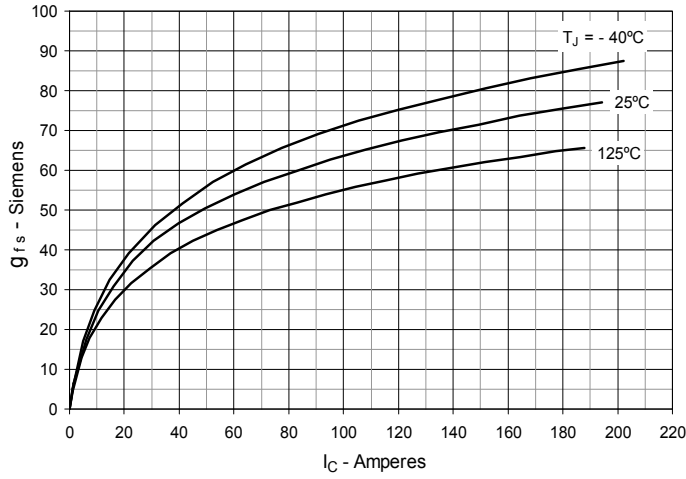


Fig. 8. Gate Charge

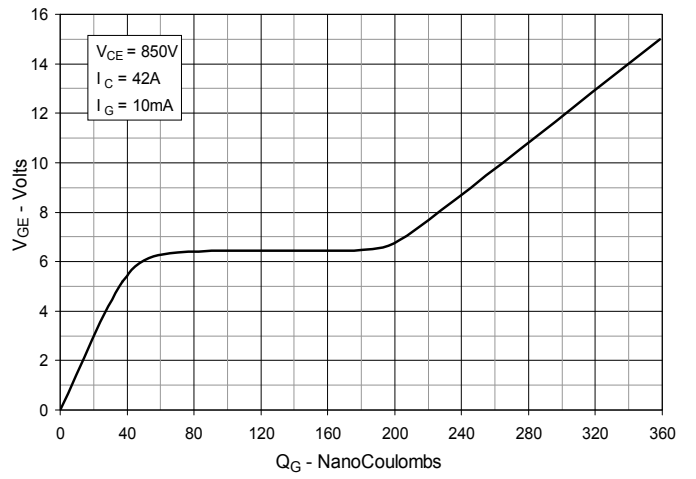


Fig. 9. Forward Voltage Drop of Intrinsic Diode

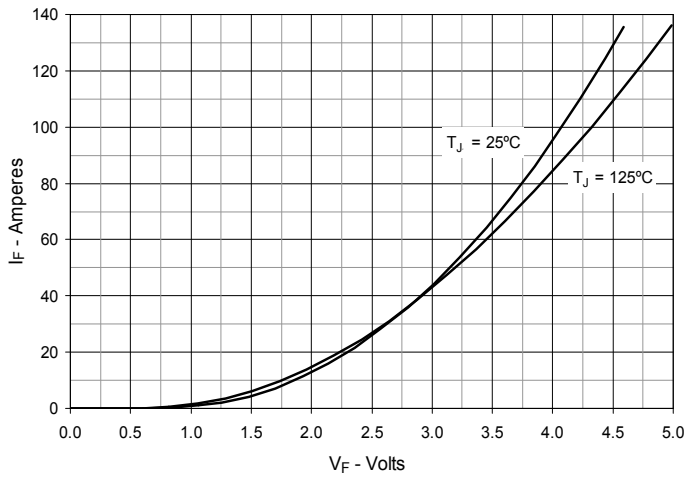


Fig. 10. Capacitance

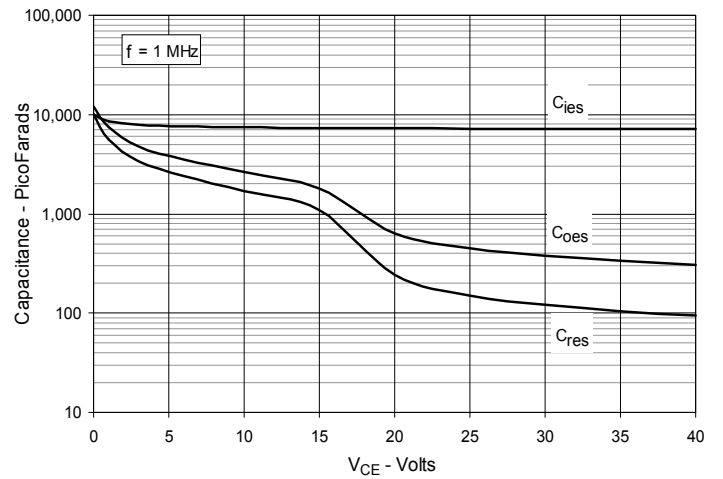


Fig. 11. Reverse-Bias Safe Operating Area

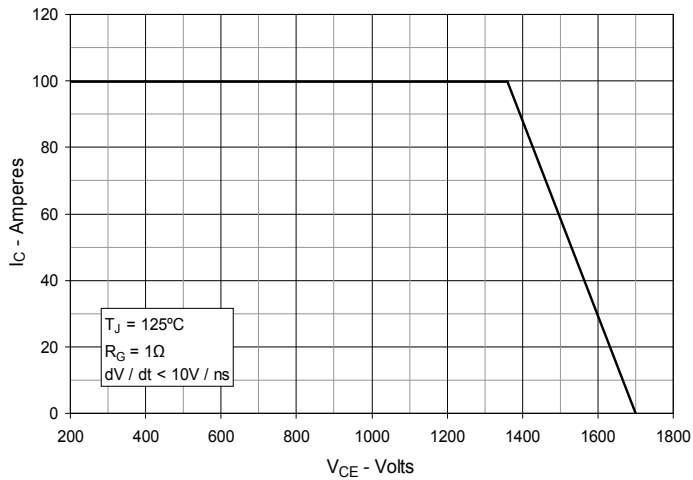


Fig. 12. Maximum Transient Thermal Impedance

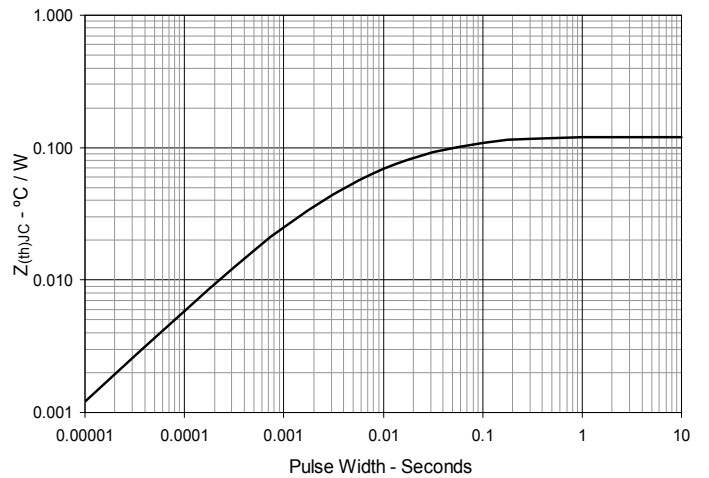


Fig. 13. Inductive Turn-off
Switching Energy Loss vs. Gate Resistance

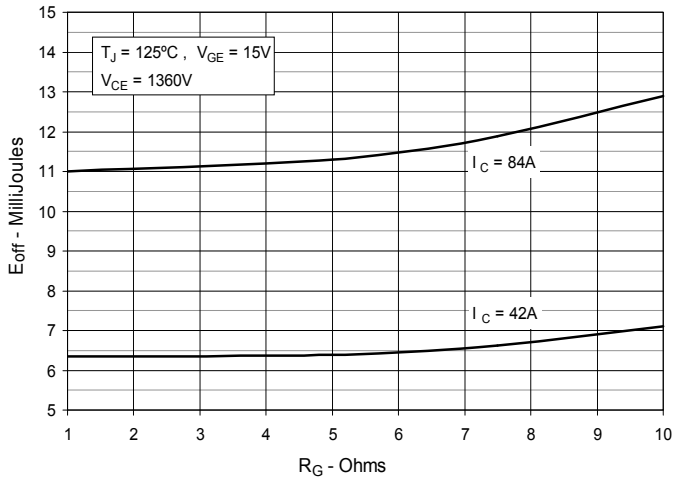


Fig. 14. Inductive Turn-off
Switching Energy Loss vs. Collector Current

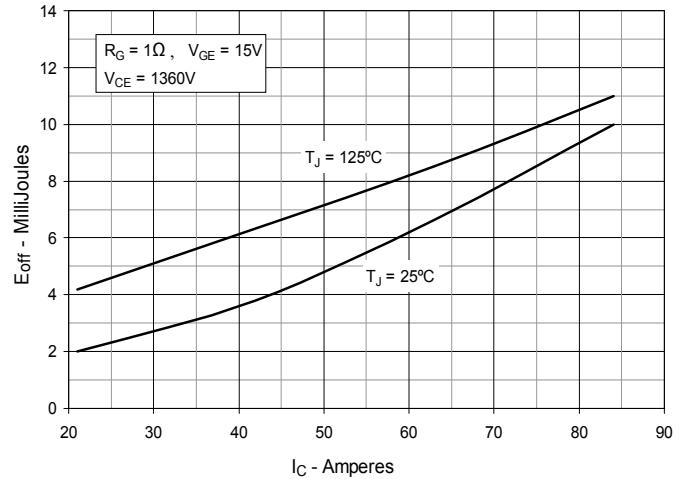


Fig. 15. Inductive Turn-off
Switching Energy Loss vs. Junction Temperature

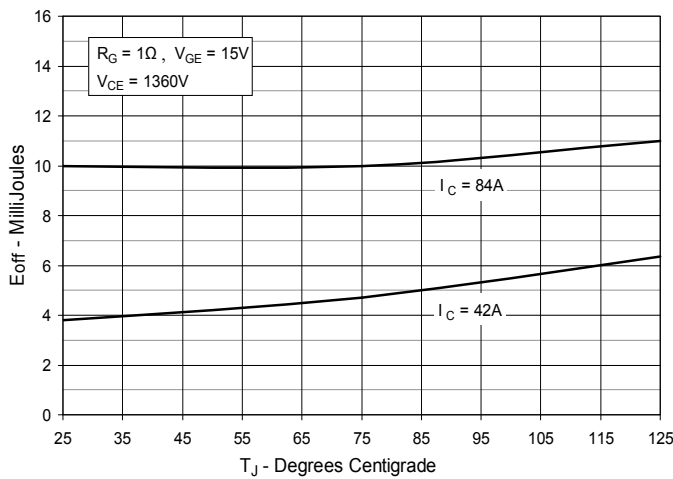


Fig. 16. Inductive Turn-off
Switching Times vs. Gate Resistance

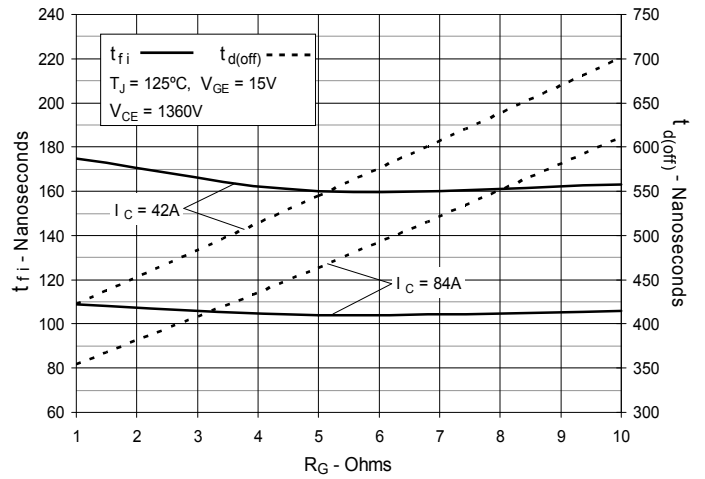


Fig. 17. Inductive Turn-off
Switching Times vs. Collector Current

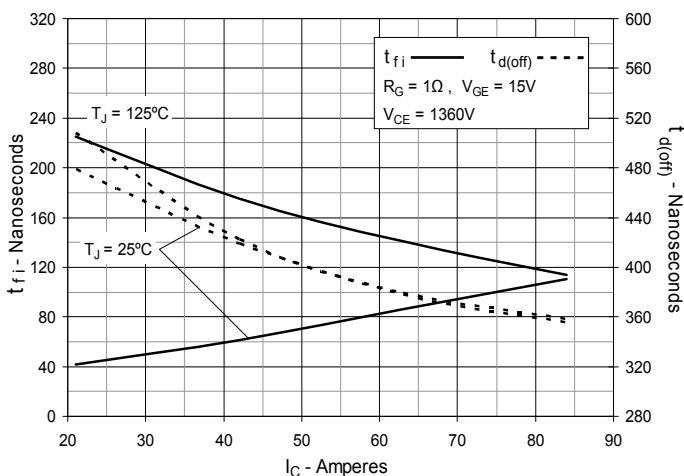
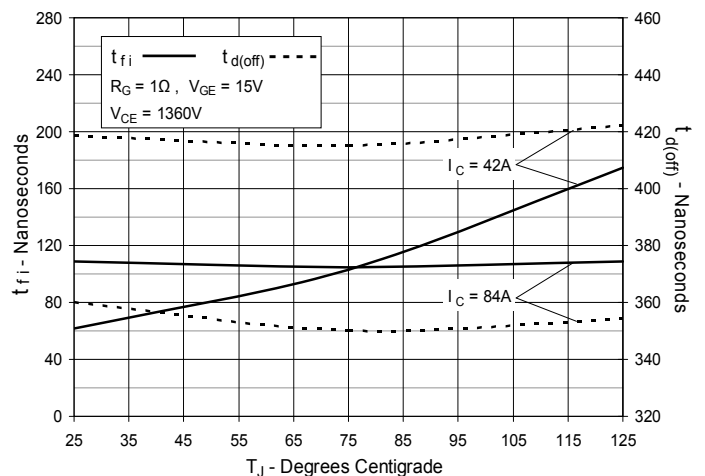
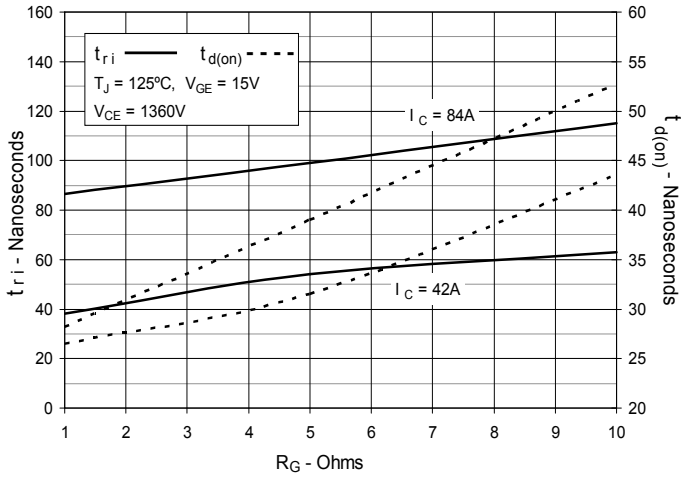


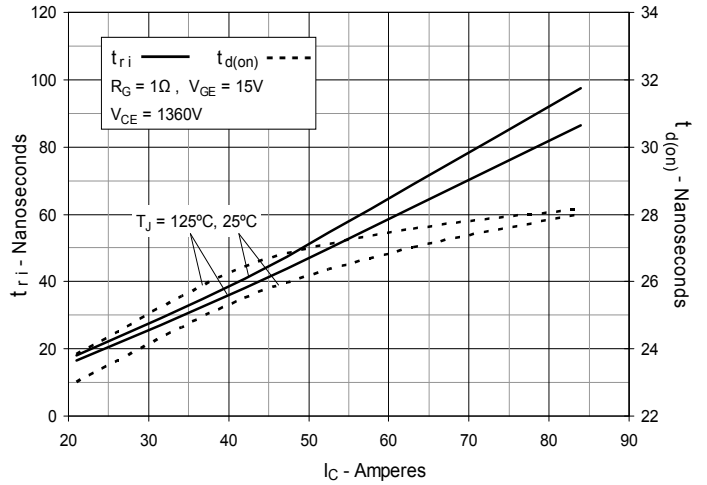
Fig. 18. Inductive Turn-off
Switching Times vs. Junction Temperature



**Fig. 19. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 20. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 21. Inductive Turn-on
Switching Times vs. Junction Temperature**

